Appl. No : 10/697,745

Amdt. dated : 07/11/05

Reply to Office Action of 06/03/05

Amendments to the Specification

1) page 14, third paragraph, please replace this paragraph with the following text:

The newly created composition of layer 14 is highlighted as layers 22 in the cross section of Fig. 2[[,]]. the layer 20

Layer 14 remains unchanged in the not exposed to photo energy regions of layer 14 that are not exposed to photo energy,

[[also]] as highlighted in the cross section of Fig. 2.

2) page 17, last paragraph, please replace this paragraph with the following text:

By now developing the exposed portions 34 of the first PAD layer 26, that is removing the second PAD layer from regions 34 highlighted in the cross section of Fig. 6, the cross section of Fig. 7 is obtained wherein first openings 32' have been created through the [[first]] second layer 26 of PAD. These opening 32' will at a later time be recognized as being the trenches of a dual damascene structure.

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3) page 19, second paragraph, please replace this paragraph with the following text:

As a final step, the results of which are shown in the cross section of Fig. 10, the layer of ARC is removed from the bottom of openings 32'/40', preventing providing a low-resistance electrical opening connection between the bottom metal layer 10 and the overlying dual damascene circuits interconnects, which are created in accordance with the second embodiment of the invention by filling openings 32'/40' with a conductive material.